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[Title of Invention] MANUFACTURING METHOD FOR ORGANIC
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[Title of the Invention] MANUFACTURING METHOD FOR ORGANIC ELECTROLUMINESCENCE DEVICE, AND ELECTRONIC DEVICE

[Claims]

[Claim 1]

A manufacturing method for an organic electroluminescence device comprising luminescent layers between an anode and a cathode, which are arranged opposite to each other, the method comprising:

forming electron transport layers, by introducing an electron transport layer forming material in a liquid phase process between the luminescent layers and the cathode, the electron transport layer forming material including a prescribed element that is selected from among a halide or an oxide of an alkali metal, an alkali earth metal, and a rare earth metal.

[Claim 2]

The manufacturing method for an organic electroluminescence device according to claim 1, wherein the liquid phase process corresponds to a liquid-drop discharge process.

[Claim 3]

The manufacturing method for an organic electroluminescence device according to claim 1 or 2, wherein the first electron transport layer forming material is made of a dispersion solution in which LiF particulates are dispersed.

[Claim 4]

The manufacturing method for an organic electroluminescence device according to claim 1 or 2, wherein the electron transport layer forming material is made of an aqueous solution in which a prescribed element selected from among a halide or an oxide of an alkali metal, an alkali earth metal, and a rare earth metal is dissolved into water.

[Claim 5]

An electronic device including an organic electroluminescence device which is manufactured by a manufacturing method according to any one of claims 1 to 4.

[Detailed Description of the Invention]

[0001]

[Technical Field of the Invention]

This invention relates to manufacturing methods for organic electroluminescence (EL) devices, and also relates to electronic devices using them.

[0002]

[Prior Art]

In general, organic electroluminescence (EL) components adapted to organic electroluminescence devices have structures in which organic luminescent materials are arranged as thin films sandwiched between anodes and cathodes, wherein electrons and holes injected by both electrodes are reunified in luminescent layers, thus causing excitation of energy to emit light. These organic electroluminescence devices have relatively high charge injection barriers between electrodes and luminescent layers. For this reason, they normally use the laminated structure comprising hole transport layers (or hole injection layers) serving as anode buffer layers and electron transport layers (or electron injection layers) serving as cathode buffer layers. In this laminated structure, the electron transport layer is in particular composed of lithium fluoride (LiF) or magnesium oxide (MgO), whereby it is possible to produce an organic electroluminescence device actualizing low-voltage drive (for example, refer to Non-Patent Literature 1).

[0003]

Presently, organic luminescent materials used for electroluminescence devices are mainly classified into two groups, namely, a low-molecular group and a high-molecular group. Organic luminescent materials of the low-molecular group are normally subjected to the gaseous phase process such as the vacuum evaporation to form thin films, which are then subjected to patterning using masks (for example, refer to Non-Patent Literature 2). Organic luminescent materials of the polymer group can

be dissolved in solvents, so that they are subjected to the application method to form films, which are then subjected to patterning by the liquid-drop discharge method such as the inkjet method (for example, refer to Non-Patent Literature 3). Manufacturing methods for an organic electroluminescence device formed by the liquid-drop discharge method are known (for example, refer to Patent Literature 1).

Materials that can be subjected to the application method to form film have been developed with respect to hole transport layers serving as anode buffer layers, which allows formation of films by a gaseous process (for example, refer to Non-Patent Literature 4).

[0004]

The vacuum evaporation method is normally used for the formation of films with respect to electron transport layers serving as cathode buffer layers. However, this may increase the manufacturing cost in terms of energy consumption and supply of materials. In addition, this may cause an unwanted factor interfering enlargement of sizes of substrates for organic electroluminescence devices, which will be practically used and incorporated into displays in the future. When organic electroluminescence devices are formed by the gaseous process, organic substance beds or substrates must be exposed to high-temperature environments; therefore, various problems such as deterioration of luminescence characteristics and deformation of substrates may occur in the case of prescribed materials having poor heat resistance.

On the contrary, when electron transport layers are formed on luminescent layers in the liquid phase, luminescent layers serving as beds therefor must be dissolved due to some solvent actually used.

[0005]

Various examples have been developed with respect to the formation of cathode buffer layers (serving as electron transport layers) in the liquid phase process. For example, Patent Literature 2 discloses the method in which layers are formed by the wet method using polymers having electron transportability (where one to five alkyl or alkoxy elements are included in each repeat unit) that are dissolved or dispersed. In addition, for example, Patent Literature 3 discloses the method in which electron injection layers are formed by the wet method using the solution (or dispersed solution) in which tetrahydro-aluminate elements are dissolved or dispersed.

[0006]

[Patent Literature 1]

Japanese Unexamined Patent Application, First Publication No. H10-12377.

[Patent Literature 2]

Japanese Unexamined Patent Application, First Publication No. 2000-252076

[Patent Literature 3]

Japanese Unexamined Patent Application, First Publication No. 2000-252079

[Non-Patent Literature 1]

Applied Physics Letters, Vol. 70 (1997), page 152

[Non-Patent Literature 2]

Applied Physics Letters, Vol. 51 (1997), page 34

[Non-Patent Literature 3]

Applied Physics Letters, Vol. 71 (1997), page 34

[Non-Patent Literature 4]

Nature, Vol. 357, page 477

[0007]

[Problems to be Solved by the Invention]

The conventional examples regarding the formation of electron transport layers in the liquid phase process fail to disclose the formation of electron transport layers that are formed in the liquid phase process using alkali metals and alkali earth metals, which produce good results in the conventional gaseous process, as well as halides (e.g., LiF) and oxides of rare earth metals.

[0008]

It is an object of the invention to provide a manufacturing method for an organic electroluminescence device in which prescribed layers are formed in the liquid phase process using alkali metals and alkali earth metals, which produce good results in the conventional gaseous process, as well as halides (e.g., LiF) and oxides of rare earth metals. It is another object of the invention to provide an electronic device using the aforementioned organic electroluminescence device.

[0009]

[Means for Solving the Problem]

In order to solve the above described problems, there is provided a

manufacturing method for an organic electroluminescence device comprising luminescent layers between an anode and a cathode, which are arranged opposite to each other, the method including forming electron transport layers, by introducing an electron transport layer forming material in a liquid phase process between the luminescent layers and the cathode, the electron transport layer forming material including a prescribed element that is selected from among a halide or an oxide of an alkali metal, an alkali earth metal, and a rare earth metal.

In accordance with this method for manufacturing an organic electroluminescence device, the electron transport layers are formed in the liquid phase process, by introducing the prescribed element that is selected from among a halide or an oxide of an alkali metal, an alkali earth metal, and a rare earth metal as the electron transport layer forming material. Therefore, it is possible to eliminate the foregoing drawbacks, which are caused in the case of the formation gaseous phase process, such as unwanted cost increase, and unwanted exposure of the organic bed material and substrate in a high-temperature environment.

[0010]

In this method for manufacturing an organic electroluminescence device, it is preferable that the liquid phase process correspond to a liquid-drop discharge process.

Therefore, since the selective application of the electron transport layer forming material can be performed by the liquid-drop discharge method, it is possible to selectively form the electron transport layers on the blue-color luminescent layer.

[0011]

In this method for manufacturing an organic electroluminescence device, it is preferable that the electron transport layer forming material be made of a dispersion solution in which LiF particulates are dispersed.

In a conventional organic electroluminescence device, LiF is used for an electron transport layer corresponding to a blue-color luminescent layer. LiF dissolves poorly in water and other solvents. Therefore, a gaseous process such as vacuum evaporation is adopted in the conventional art, but a liquid phase process is not adopted.

The inventors consider it preferable to adopt the liquid phase process, in which LiF is transformed into micro particulates whose diameters are 1μm or less, for example, and the micro particulates are dispersed into a polar solvent (or dispersion medium)

such as water, and the liquid matter is arranged at a predetermined position by way of a liquid-drop discharge method.

By forming electron transport layers made of LiF in a liquid phase process, it is possible to eliminate the foregoing drawbacks, which are caused in the case of the formation gaseous phase process, and to manufacture an organic electroluminescence device having high efficiency in light emission.

[0012]

In this method for manufacturing an organic electroluminescence device, the electron transport layer forming material can be made of an aqueous solution in which a prescribed element selected from among a halide or an oxide of an alkali metal, an alkali earth metal, and a rare earth metal is dissolved into water.

In the case in which a nonpolar solvent is used and the aqueous solution is introduced on the luminescent layers, the aqueous solution does not dissolve the luminescent layers. Therefore, the electron transport layers can be formed in the liquid phase process without diminishing the performance of the luminescent layer.

[0013]

An electronic device of the invention includes an organic electroluminescence device which is manufactured by the above described manufacturing method.

In this electronic device, the foregoing drawbacks of the organic electroluminescence device, which are caused in the case of the formation gaseous phase process, such as unwanted cost increase, and unwanted exposure of the organic bed material and substrate in a high-temperature environment, are eliminated. Therefore, it is possible to reduce the cost and improve the reliability of the electronic device.

[0014]

[Embodiments of the Invention]

Hereinafter, this invention will be concretely described.

Before specifically describing a manufacturing method for an organic electroluminescence device in accordance with this invention, the wiring structure adapted to the organic electroluminescence device will be described with reference to FIG. 1.

FIG. 1 is a simple wiring diagram showing an organic electroluminescence

device 1 of an active matrix type using thin film transistors (TFTs) as switching elements.

[0015]

The organic electroluminescence device 1 of FIG. 1 comprises a plurality of scan lines 101 and a plurality of signal lines 102, which are wired to rectangularly intersect each other, as well as a plurality of power supply lines 103 that are wired in parallel with the signal lines 102. In addition, pixel regions X are arranged in proximity to intersecting points between the scan lines 101 and the signal lines 102 respectively.

All the signal lines 102 are connected with a data line drive circuit 100 comprising shift registers, level shifters, video lines, and analog switches. All the scan lines 101 are connected with a scan line drive circuit 80 comprising shift registers and level shifters.

[0016]

Each of the pixel regions X provides a switching TFT 112 whose gate electrode is supplied with a scanning signal via the scan line 101, a capacitance element 113 for holding a pixel signal supplied from the signal line 102 via the switching TFT 112, a driving TFT 123 whose gate electrode is supplied with the pixel signal held by the capacitance element 113, a pixel electrode (i.e., an anode) into which a drive current flows from the power supply line 103 when electrically connected with the power supply line 103 via the driving TFT 123, and a function layer 110 that is sandwiched between the pixel electrode 23 and a cathode 50. A luminescence component (i.e., an organic electroluminescence component) is constituted by the pixel electrode 23, cathode 50, and function layer 110.

[0017]

In the organic electroluminescence device 1, when the scan line 101 is driven to turn on the switching TFT 112, an electric potential of the signal line 102 is held by the capacitance element 113, so that on/off states of the driving TFT 123 depends upon the state of the capacitance element 113. Then, a current flows from the power supply line 103 to the pixel electrode 23 via a channel of the driving TFT 123, and it further flows into the cathode 50 via the function layer 110. Thus, the function layer 110 emits light in response to an amount of current flowing therethrough.

[0018]

Next, the structure of the organic electroluminescence device 1 will be described with reference to FIGS. 2 to 5.

As shown in FIG 2, the organic electroluminescence device 1 comprises a substrate 20 having light transmission ability and electrical insulation ability, a pixel electrode area (not shown) in which pixel electrodes connected with switching TFTs (not shown) are arranged in a matrix form on the substrate 20, power supply lines (not shown) that are arranged in the periphery of the pixel electrode regions and are connected with the pixel electrodes, and a pixel portion 3 having a substantially rectangular shape in plan view (encompassed by single-dashed lines in FIG. 2) that is located on or above the pixel electrode region. In addition, the pixel portion 3 is partitioned into a real display area 4 (encompassed by double-dashed lines in FIG. 2) located at the center area thereof, and a dummy area 5 (defined between single-dashed lines and double-dashed lines) that is arranged in the periphery of the real display area 4.

[0019]

Numerous display regions R, G, and B (representing read, green and blue colors) having electrodes respectively are arranged in the real display area 4 in such a way that they are independently separated from each other in A-B directions and C-D directions.

A pair of scan line drive circuits 80 are arranged on both sides of the real display area 4 and are arranged beneath the dummy area 5.

[0020]

An inspection circuit 90 is arranged in the upper side of the real display area 4 in order to inspect operating conditions of the organic electroluminescence device 1. It comprises an inspection information output means (not shown) for outputting inspection results to an external device and the like. Thus, it is possible to perform inspection as to the quality and defects of the display device while manufactured or when forwarded to shipment. The inspection circuit 90 is arranged beneath the dummy area 5.

[0021]

A power supply unit (not shown) applies drive voltages to the scan line drive circuits 80 and the inspection circuit 90 via drive voltage conductors 310 (see FIG. 3)

and drive voltage conductors 340 (see FIG. 4) respectively. In addition, a main driver (not shown) for controlling the overall operation of the organic electroluminescence device 1 transmits and applies drive control signals and drive voltages to the scan line drive circuits 80 and the inspection circuit 90 via drive control signal conductors 320 (see FIG. 3) and drive voltage conductors 350 (see FIG. 4) respectively. Herein, drive control signals are instruction signals from the main driver, which are related to controls for the scan line drive circuits 80 and the inspection circuit 90 to output signals.

[0022]

As shown in FIGS. 3 and 4, the overall structure of the organic electroluminescence device 1 is constituted by joining together a substrate 20 and an encapsulating substrate 30 via an enclosing resin 40. In the space encompassed by the substrate 20, the encapsulating substrate 30, and the enclosing resin 40, a dryer (or a drying agent) 45 is bonded onto the interior wall of the encapsulating substrate 30. This space is filled with nitrogen gas to form a nitrogen gas filled layer 46. Due to the aforementioned structure, it is possible to reliably prevent water content and oxygen from infiltrating into the inside of the organic electroluminescence device 1. Thus, it is possible to increase the lifetime of the organic electroluminescence device 1.

Incidentally, it is possible to replace the dryer 45 with a getter (agent), for example.

[0023]

In the case of an organic electroluminescence device of a so-called top emission type, emitted light is output from the encapsulating substrate 30 arranged opposite to the substrate 20; therefore, it is possible to use either a transparent substrate or an opaque substrate for the substrate 20. Various examples can be listed as the opaque substrate, for example, a substrate in which an insulating process such as the surface oxidation is performed on a ceramic material made of alumina or a metal sheet made of stainless steel, and a substrate made of a thermosetting resin or a thermoplastic resin.

In the case of an organic electroluminescence device of the so-called back emission type, emitted light is output from the substrate 20; therefore, it is possible to use either a transparent substrate or a semitransparent substrate for the substrate 20. For example, it is possible to list prescribed materials such as glass, quartz, and resin (e.g., plastics, and plastic films) for the substrate 20, wherein a glass substrate is

preferably used in particular. The present embodiment is of the back emission type in which emitted light is output from the substrate 20; therefore, the transparent or semitransparent substrate is used as the substrate 20.

In addition, it is possible to use a plate-like member having an electrically insulating ability for the encapsulating substrate 30, for example. Furthermore, the enclosing resin 40 is made of a thermosetting resin or an ultraviolet-setting resin, for example. In particular, it is preferable to use an epoxy resin, which is one type of the thermosetting resin, for the enclosing resin 40.

[0024]

A circuit layer 11 including the driving TFTs 123 for driving the pixel electrodes 23 is formed on the substrate 20. Luminescent components (e.g., organic electroluminescence components) are arranged on the circuit layer 11. As shown in FIG. 5, the luminescent component is constituted by sequentially forming a pixel electrode 23 serving as an anode, a hole transport layer 70 for injecting or transporting holes from the pixel electrode 23, a luminescent layer 60 comprising organic electroluminescent substance, which is one type of the electroluminescent substances, and a cathode 50.

[0025]

As shown in FIG. 2, the organic electroluminescence device 1 provides three types of luminescent dots, i.e., red (R), green (G), and blue (B) dots, in the real display area 4, thus actualizing a full-color display. Among these dots, as shown in FIG. 5, electron transport layers 65B for a blue (B) color illuminating dot for injecting or transporting electrons from the cathode 50 is formed between the luminescent layer 60 and the cathode 50. This is based on the reason why, among red, green, and blue colors, charge injection barriers between the cathode 50 and the luminescent layer 60 for blue color is higher than the one for red or green color.

[0026]

Of course, this invention is not necessarily limited to providing the electron transport layers only for blue color. The electron transport layers can be provided for a red or green color illuminating dot.

In the luminescent component having the aforementioned structure, holes injected from the hole transport layer 70 are coupled with electrons from the cathode 50

in the luminescent layer 60, which is thus activated to cause light emission. Specifically, an electron from the cathode 50 is transported into the luminescent layer 60 via the electron transport layer 65B with respect to a blue dot. Thus, it is possible to further increase the electron transport efficiency.

[0027]

In the present embodiment that is of the back emission type, the pixel electrode 23 serving as the anode is formed using a prescribed transparent conductive material, for which indium-tin oxide (ITO) can be preferably used. In addition, it is possible to use other materials such as amorphous transparent conductive films composed of prescribed elements regarding indium oxide and zinc oxide (namely, 'IZO' which is a registered trademark, produced by Idemitsu-Kosan Co., Ltd.), for example. For the sake of convenience, the present embodiment uses ITO; instead, it is possible to use other elements such as Pt, Ir, Ni, and Pd.

[0028]

It is preferable that the pixel electrode 23 have a prescribed thickness ranging from 50 nm to 200 nm, wherein it is preferable to set the thickness to approximately 150 nm. Oxygen (O₂) plasma processing is performed on the surface of the ITO serving as the pixel electrode 23, whereby a lyophilic characteristic is applied to the pixel electrode 23, which is also cleaned on the surface and is adjusted in work function. The O₂ plasma processing is performed under prescribed conditions in which plasma power ranges from 100 kW to 800 kW, oxygen gas flow ranges from 50 ml/min to 100 ml/min, substrate carrying speed ranges from 0.5 mm/sec to 10 mm/sec, and substrate temperature ranges from 70 °C to 90 °C.

[0029]

The hole transport layer 70 is formed using the material in which polystyrene sulfonic acid is added to polythiophene derivative or polypyrrole derivative. Specifically, as the material used for the formation of the hole transport layer 70, it is preferable to use the dispersion solution mixing 3,4-polyethylene diothiophene (PEDOT) and polystyrene sulfonic acid (PSS) at a mixing ratio of PEDOT/PSS=1/20 (product name: Bytron-p produced by Byer Co. Ltd.), that is, the dispersion solution in which 3,4-polyethylene diothiophene is dispersed in polystyrene sulfonic acid serving as a dispersion medium and is further dispersed into water serving as a polar solvent (or

dispersion medium).

[0030]

As the polar solvent (or dispersion medium), it is possible to use prescribed substances, instead of water, such as isopropyl alcohol (IPA), normal butanol, γ -butyrolactone, N-methyl-pyrolidone (NMP), 1-, 3-dimethyl-2-imidazolidinone (DMI) and derivatives thereof as well as carbitol-acetate and glycolic ether such as butyl-carbitol-acetate.

The material used for the formation of the hole transport layer is not necessarily limited to the aforementioned ones; hence, it is possible to use various kinds of elements. For example, it is possible to use the dispersion solution in which a prescribed element such as polystyrene, polypyrrole, polyaniline, polyacetylene and derivatives thereof are dispersed into an appropriate dispersion medium such as polystyrene sulfonic acid.

[0031]

As the material used for the formation of the luminescent layer 60, it is possible to use known luminescent materials capable of generating fluorescence or phosphorescence. Specifically, it is possible to use a prescribed polymer such as (poly)-paraphenylene-vinylene derivative, polyphenylene derivative, polyfluorene derivative, polyvinyl-carbazole, polythyophene derivative, penylene pigment, coumalin pigment, and rhodamine pigment; or it is possible to use a prescribed element realized by doping rublene, penylene, 9-, 10-diphenylanthracene, tetraphenylbutadiene, Nilered, coumalin 6, or quiaklydon into the aforementioned polymers, for example.

[0032]

As the solvent liquefying the aforementioned materials, a prescribed nonpolar solvent insoluble to the hole transport layer 70 is used in order to avoid re-dissolution of the hole transport layer 70. In particular, in the case in which the application of the material used for the formation of the luminescent layer is performed by the liquid-drop discharge method such as the inkjet method (details of which will be described later), as the aforementioned nonpolar solvent, it is preferable to use dihydro-benzofuran, trimethylbenzene, tetramethylbenzene, cyclohexylbenzene, or their mixture. In the case in which the application is performed by the spin-coat method or dip method, it is preferable to use toluene, xylene, and the like.

[0033]

The electron transport layer 65G is formed using a prescribed material such as alkali metal, alkali earth metal, and halide or oxide of rare earth metal. For example, a prescribed element such as Li, Na, and Cs is used for the alkali metal; a prescribed element such as Ca, Ba, and Sr is used for the alkali earth metal; and a prescribed element such as Sm, Tb, and Er is used for the rare earth metal. These metals are preferably transformed into fluoride. Alternatively, they can be transformed into other halides (i.e., chlorides and bromides) or oxides.

[0034]

Among compounds used as the material for the electron transport layer 65B, prescribed compounds allowing evaporation using LiF and the like can be transformed into micro particulates whose diameters are 1 μm or less by the gaseous evaporation method such as the solvent trap method and cold trap method, details are disclosed in the paper entitled “explication for dispersion and aggregation, and applied technology therefor” (1992), page 30, for example. That is, micro particulates are uniformly dispersed in the dispersion medium so as to produce the dispersion solution (or colloid). This allows application to be performed by the liquid-drop discharge method; that is, this allows film formation to be realized in the liquid phase process.

[0035]

It is preferable that the thickness of the electron transport layer 65B made of the aforementioned compound range from 0.5 nm to 10 nm; in particular, it is preferable to form a very thin film having a thickness of 5 nm or less. In addition, it is preferable to form the electron transport layer 65B by the liquid-drop discharge method such as the inkjet method (details of which will be described later) because in the case of the application of the dispersion solution, a thin film can be formed at a thickness on the order of several nano meters. Furthermore, as the dispersion medium used for the dispersion of the aforementioned micro particulates, it is preferable to use water, methanol, ethanol, propanol, isopropyl alcohol (IPA), and polar solvent such as dimethylketone because these elements do not cause re-dissolution of the luminescent layer 60.

[0036]

In an exceptional case in where the luminescent layer 60 is dissolved into the

polar solvent, it is preferable to use a nonpolar solvent such as toluene, xylene, benzene, hexane, cyclohexane, tetradecane, and iso-octane.

Among the materials that can be used for the formation of the electron transport layer 65B, some fluorides including Na, K, Rb, and Cs show water solubility. They are solubilized by being dissolved into the polar solvent (or nonpolar solvent exceptionally used depending on the type of the luminescent layer 60), thus allowing application by the liquid-drop discharge method to be performed, i.e., film formation by the liquid phase process to be performed.

[0037]

Specifically, it is possible to list precise examples such as LiF and NaF serving as the material used for the formation of the electron transport layer 65, so that specific producing methods therefor will be described below.

(LiF)

First, micro particulates, composed of lithium fluoride (LiF) and having diameters substantially on the order of nano meter are produced by the gaseous evaporation method such as the solvent trap method and cold trap method. Then, micro particulates are uniformly dispersed in water to produce a dispersion solution (or colloid).

The aforementioned dispersion solution is applied onto the blue-color luminescent layer composed of the polyfluorene material by the inkjet method (or liquid-drop discharge method), so that its film thickness is approximately set to 5 nm. Herein, no bad influence such as re-dissolution is detected with respect to the luminescent layer 60.

In addition, it is confirmed that the same effect of the LiF film formed by the conventional vacuum evaporation method can be obtained with respect to the electron transport layer 65B made of the LiF film that is formed in the liquid phase process described above.

[0038]

(NaF)

Sodium fluoride (NaF) is soluble because of its solubility of 4.15 g per 100 g water (25 °C). Herein, it is unnecessary to prepare micro particulates dispersed into the dispersion solution; therefore, it is possible to realize application using aqueous

solution thereof. That is, a saturated solution of NaF is diluted with polyvinyl alcohol (PVA) so as to produce a prescribed solution, which is applied to form a good thin film by the liquid-drop discharge method and the spin-coat method, for example.

By applying the aforementioned solution, which is produced by diluting NaF with PVA, onto the blue-color luminescent layer composed of polyfulorene material, it is confirmed that the electron transport layer 65B can produce expected effects.

[0039]

As shown in FIGS. 3 to 5, the overall area of the cathode 50 is larger than the total of the real display area 4 and the dummy area 5; therefore, the cathode 50 is arranged to comprehensively cover both the real display area 4 and the dummy area 5.

It is preferable to select a prescribed material (e.g., Ca and Mg) having a low work function for the material used for the formation of the lower portion of the cathode 50 positioned close to the luminescent layer 60. On the other hand, another material (e.g., Al) having a high work function is used for the formation of the upper portion (or enclosed side) of the cathode 50. Preferably, the thickness of the cathode 50 ranges from 100 nm to 1000 nm; in particular, it preferably ranges from 200 nm to 500 nm. Because it is a back emission type, the present embodiment does not necessarily adopt light transmissive cathode 50.

[0040]

As shown in FIG 5, the circuit layer 11 is arranged beneath the aforementioned luminescence component and is formed on or above the substrate 20. Specifically, a bed mainly composed of SiO₂ is formed as a surface protective layer 281 on the surface of the substrate 20; and a silicon layer 241 is formed on the bed. In addition, a gate insulating layer 282 mainly composed of SiO₂ and/or SiN is formed on the surface of the silicon layer 241.

[0041]

The silicon layer 241 contains a channel region 241a that is sandwiched between the gate insulating layers 282 and is arranged to vertically match a gate electrode 242 in position. The gate electrode 242 constructs a part of the aforementioned scan line 101 (not shown). In addition, a first interlayer insulating layer 283 mainly composed of SiO₂ is arranged to cover the silicon layer 241 and is formed on the surface of the gate insulating layer 282 providing the gate electrode 242.

[0042]

A low-concentration source region 241b and a high-concentration source region 241S are arranged in the source side of the channel region 241a inside of the silicon layer 241. In addition, a low-concentration drain region 241c and a high-concentration drain region 241D are arranged in the drain side of the channel region 241a inside of the silicon layer 241. This establishes a so-called light doped drain (LDD) structure. The high-concentration source region 241S is connected to a source electrode 243 via a contact hole 243a that is opened to penetrate through the gate insulating layer 282 and the first interlayer insulating layer 283. The source electrode 243 constructs a part of the aforementioned power supply line 103 (see FIG. 1), which is elongated in a direction three-dimensionally perpendicular to the drawing sheet of FIG. 5 at the position of the source electrode 243. In addition, the high-concentration drain region 241D is connected to a drain electrode 244, which is formed in the same layer of the source electrode 243, via a contact hole 244a that is opened to penetrate through the gate insulating layer 282 and the first interlayer insulating layer 283.

[0043]

The upper portion of the first interlayer insulating layer 283 in which the source electrode 243 and the drain electrode 244 is covered with a second interlayer insulating layer 284 mainly composed of an acrylic resin component. As the material used for the formation of the second interlayer insulating layer 284, it is possible to use other materials, other than acrylic insulating materials, such as SiN and SiO₂. The pixel electrode 23 composed of ITO is formed on the surface of the second interlayer insulating layer 284 and is connected to the drain electrode 244 via a contact hole 23a that is formed to penetrate through the second interlayer insulating layer 284. That is, the pixel electrode 23 is connected to the high-concentration drain region 241D of the silicon layer 241 via the drain electrode 244.

[0044]

Numerous TFTs (i.e., driving TFTs) are contained in the scan line drive circuit 80 and the inspection circuit 90, wherein n-channel and/or p-channel TFTs are used to constitute inverters included in shift registers. Each of these TFTs has substantially the same structure of the aforementioned driving TFT 123, except that it is not connected with the pixel electrode 23.

[0045]

The surface of the second interlayer insulating layer 284 on which the pixel electrode 23 is formed is covered with the pixel electrode 23, a lyophilic control layer 25 mainly composed of a lyophilic material such as SiO₂, and an organic bank layer 221 composed of acrylic or polyimide. An opening 25a is formed in the lyophilic control layer 25, and an opening 221a is formed in the organic bank layer 221. In each of these openings 25a and 221a, the hole transport layer 70 and the luminescent layer 60 are sequentially laminated in an order counting from the pixel electrode 23. In the present embodiment, the lyophilic control layer 25 has a higher lyophilic property compared with acrylic and polyimide materials forming the organic bank layer 221.

The aforementioned layers ranging from the substrate 20 to the second interlayer insulating layer 284 are collected to form the circuit layer 11.

[0046]

In order to actualize a color display, the organic electroluminescence device 1 of the present embodiment is designed such that the luminescent layers 60 are formed to suit three primary colors in emission wavelength bands thereof. For example, there are provided a red-color luminescent layer 60R whose emission wavelength band matches red color, a green-color luminescent layer 60G whose emission wavelength band matches green color, and a blue-color luminescent layer 60B whose emission wavelength band matches blue color, which are respectively allocated to display regions R, G, and B. Therefore, a single pixel is constituted by these display regions R, G, and B. A black matrix (BM, not shown) is formed by sputtering metallic chrome in boundaries between colored display regions and is located between the organic bank layer 221 and the lyophilic control layer 25.

[0047]

Next, a manufacturing method for the organic electroluminescence device 1 of the present embodiment will be described with reference to FIGS. 6 to 10, each of which is a cross sectional view taken along line A-B in FIG. 2.

First, as shown in FIG. 6(a), a surface protective layer 281 is formed on the surface of the substrate 20. Next, amorphous silicon layer 501 is formed on the surface protective layer 281 by the ICVD method or plasma CVD method (where 'CVD' stands for 'chemical-vapor deposition'). Then, the laser annealing method or

rapid heating method is performed to cause growth of crystal grains, thus forming a polysilicon layer.

[0048]

Next, as shown in FIG. 6(b), the polysilicon layer is subjected to patterning by the photolithography method, thus forming island-like silicon layers 241, 251, and 261. The silicon layers 241 are formed in the aforementioned display area so as to form the driving TFT connected with the pixel electrode 23. The other silicon layers 251 and 261 are respectively used to form p-channel and n-channel TFTs contained in the scan line drive circuit 80.

[0049]

Next, the plasma CVD method or thermal oxidation method is performed using a silicon oxide film whose thickness approximately ranges from 30 nm to 200 nm so as to form a gate insulating layer 282, which is arranged to cover the overall surface including the silicon layer 241, 251, and 261 and the surface protective layer 281. When the gate insulating layer 282 is formed by the thermal oxidation method, crystallization is performed on the silicon layers 241, 251, and 261, which are thus transformed into polysilicon layers.

[0050]

When channel doping is performed on the silicon layers 241, 251, and 261, boron ions are implanted at the prescribed timing with a dose rate of about $1 \times 10^{12}/\text{cm}^2$. As a result, the silicon layers 241, 251, and 261 are transformed into low-concentration p-channel silicon layers whose impurity concentration (calculated using impurities after activation annealing) is about $1 \times 10^{17}/\text{cm}^2$.

[0051]

Next, an ion implantation selection mask is partially formed in channel layers of the p-channel and n-channel TFTs. Then, phosphorus ions are implanted with a dose rate of about $1 \times 10^{15}/\text{cm}^2$. As a result, highly concentrated impurities are introduced into the patterning mask in a self-alignment manner. Thus, as shown in FIG. 6(c), a pair of a high-concentration source region 241S and a high-concentration drain region 241D are formed with respect to the silicon layer 241; similarly, a pair of a high-concentration source region 261S and a high-concentration drain region 261D are formed with respect to the silicon layer 261.

[0052]

As shown in FIG. 6(c), the overall surface of the gate insulating layer 282 is then covered with a gate electrode forming conductive layer 502, which is made of a doped silicon film or a silicide film, or which is made of a metal film such as an aluminum film, a chrome film, and a tantalum film. The thickness of the conductive layer 502 is about 500 nm. Then, as shown in FIG. 6(d), patterning is performed to form a gate electrode 252 used for the formation of a p-channel driving TFT, a gate electrode 242 used for the formation of a pixel TFT, and a gate electrode 262 used for the formation of an n-channel driving TFT. In addition, drive control signal conductors 320 (or 350) as well as first layers 121 for cathode power source lines are simultaneously formed. In this case, the drive control signal conductors 320 (or 350) are arranged in the dummy area 5.

[0053]

Subsequently, as shown in FIG. 6(d), ion implantation of phosphorus ions is performed using the gate electrodes 242, 252, and 262 as masks on the silicon layers 241, 251, and 261 at a dose rate of about $4 \times 10^{13}/\text{cm}^2$. As a result, lowly concentrated impurities are introduced into the gate electrodes 242, 252, and 262 in a self-alignment manner; therefore, as shown in FIG. 6(d), a pair of a low-concentration source region 241b and a low-concentration drain region 241c are formed with respect to the silicon layer 241, and a pair of a low-concentration source region 261b and a low-concentration drain region 261c are formed with respect to the silicon layer 261. In addition, a pair of low-concentration impurity regions 251S and 251D are formed with respect to the silicon layer 251.

[0054]

Next, as shown in FIG. 7(e), an ion implantation selection mask 503 is formed to cover the overall surface except for a prescribed region regarding the p-channel driving TFT 252. That is, ion implantation is performed using the ion implantation selection mask 503 so that boron ions are introduced into the silicon layer 251 at a dose rate of about $1.5 \times 10^{15}/\text{cm}^2$. Herein, the gate electrode 252 forming a part of the p-channel driving TFT functions as a mask, so that highly concentrated impurities are doped into the silicon layer 252 in a self-alignment manner. Therefore, both of the low-concentration impurity regions 251S and 251D are counter-doped so as to form a

source region and a drain region for the p-channel driving TFT.

[0055]

Next, as shown in FIG. 7(f), a first interlayer insulating layer 283 is formed on the overall surface of the substrate 20 and is then subjected to patterning by the photolithography method, so that contact holes C are formed at prescribed positions matching source electrodes and drain electrodes of TFTs.

[0056]

Next, as shown in FIG. 7(g), a conductive layer 504 composed of a prescribed metal such as aluminum, chrome, and tantalum is formed to cover the first interlayer insulating layer 283. The thickness of the conductive layer 504 approximately ranges from 200 nm to 800 nm. Then, patterning masks 505 are formed to cover regions 240a used for the formation of source electrodes and drain electrodes of TFTs, regions 310a used for the formation of drive voltage conductors 310 (or 340), and regions 122a used for the formation of second layers of cathode power source lines within the conductive layer 504. In addition, the conductive layer 504 is subjected to patterning so as to form source electrodes 243, 253, and 263 as well as drain electrodes 244, 254, and 264 as shown in FIG. 8(h).

[0057]

Next, as shown in FIG. 8(i), a second interlayer insulating layer 284 composed of a prescribed polymer material such as an acrylic resin is formed to cover the first interlayer insulating layer 283 containing the aforementioned elements. It is preferable that the thickness of the second interlayer insulating layer 284 approximately range from 1 μ m to 2 μ m. Instead, it is possible to form a second interlayer insulating film composed of SiN or SiO₂. Herein, the thickness of the SiN film is preferably set to 200 nm, and the thickness of the SiO₂ film is preferably set to 800 nm.

[0058]

Next, as shown in FIG. 8(j), regions corresponding to the drain regions 244 for the driving TFTs within the second interlayer insulating layer 284 are removed by etching so as to form the contact holes 23a.

Then, a transparent conductive film forming pixel electrodes 23 is formed to cover the overall surface of the substrate 20. The transparent conductive film is subjected to patterning so as to form the pixel electrodes 23, which are electrically

conducted with the drain electrodes 244 via the contact holes 23a in the second interlayer insulating layer 284, and dummy patterns 26 for the dummy area as shown in FIG. 9(k). For the sake of convenience, in FIGS. 3 and 4, the pixel electrodes 23 and the dummy patterns 26 are collectively expressed as the pixel electrodes 23.

[0059]

The dummy patterns 26 are constituted not to be connected with metal wires arranged thereunder via the second interlayer insulating layer 284. That is, the dummy patterns 26 are arranged like islands, which may substantially match the shape of the pixel electrodes 23 arranged in the real display area. Of course, they can be formed in another shape that differs from the shape of the pixel electrodes 23 arranged in the real display area. In this case, the dummy patterns 26 should include at least certain regions located above the drive voltage conductors 310 (or 340).

[0060]

Next, as shown in FIG. 9(l), a lyophilic control layer 25 serving as an insulating layer is formed on the pixel electrodes 23 and the dummy patterns 26 as well as on the second interlayer insulating layer 284. When the lyophilic control layer 25 is formed such that openings are formed at the pixel electrodes, it is possible for electrons to move from the pixel electrodes 23 in the openings 25a (see FIG. 3 and FIG. 9(m)). In contrast, when the dummy patterns 26 do not provide the openings 25a, the lyophilic control layer (or insulating layer) 25 acts as a hole movement block layer to avoid hole movement. Subsequently, a black matrix (BM, not shown) is formed and arranged in hollows that are formed in the lyophilic control layer 25 and are positioned between adjacent pixel electrodes. Specifically, sputtering is performed using metallic chrome with respect to the hollows of the lyophilic control layer 25, thus forming prescribed films.

[0061]

Next, as shown in FIG. 9(m), organic bank layers 221 are formed at prescribed positions of the lyophilic control layer 25 so as to cover the aforementioned black matrix (BM). Specifically, the organic bank layers 221 are formed in such a way that solution, in which resists composed of acrylic resin or polyimide resin are dissolved into solvent, is applied in accordance with one of various application methods such as spin-coat method and dip-coat method, thus forming organic layers. Incidentally, the

material constituting organic layers can be selected from among various materials that are not dissolved into solvent such as ink and that can be easily patterned by etching.

Subsequently, the organic layers are subjected to patterning by use of the photolithography technique or etching technique so that bank openings 221a are formed in the organic layers, wherein the wall surfaces of the organic bank layers 221 are located in the bank openings 221a. In this case, the organic bank layers 221a must contain at least certain regions located above the aforementioned drive control signal conductors 320.

[0062]

Next, lyophilic regions and lyophobic regions are formed on the surfaces of the organic bank layers 221. In the present embodiment, these regions are formed by plasma treatment, which comprises four steps; that is, a preheating step, an ink-lyophilic step for making upper surfaces of the organic bank layers 221, wall surfaces of the openings 221a, electrode surfaces 23c of the pixel electrodes 23, and the upper surface of the lyophilic control layer 25 to be lyophilic with ink, an ink-lyophobic step for making upper surfaces of the organic bank layers 221, and wall surfaces of the openings 221a to be lyophobic with ink, and a cooling step.

[0063]

That is, a prescribed base material (i.e., the substrate 20 including banks) is heated at a prescribed temperature ranging from 70 °C to 80 °C, for example; then, as the ink-lyophilic step, a plasma process (i.e., O₂ plasma process) is performed using oxygen as reaction gas in the open-air atmosphere. Then, as the ink-lyophobic step, a plasma process (i.e., CF₄ plasma process) is performed using methane tetrafluoride as reaction gas in the open-air atmosphere. Thereafter, the base material that is once heated in the plasma processes is cooled down to the room temperature, so that lyophilic property and lyophobic property can be imparted to prescribed regions.

[0064]

Incidentally, the electrode surfaces 23c of the pixel electrodes 23 and the lyophilic control layer 25 may be slightly affected by the CF₄ plasma process. However, since both of ITO, which is the designated material for the pixel electrodes 23, and SiO₂ or TiO₂, which is the designated material for the lyophilic control layer 25, have poor lyophilic property against fluorine, it is possible to maintain the lyophilic

property in the pixel electrodes 23 and the lyophilic control layer 25 because hydroxyl group applied in the ink-lyophilic step is not replaced with fluorine group.

[0065]

Next, a hole transport layer forming process is performed to form the hole transport layer 70. As the hole transport layer forming process, it is possible to use a manufacturing method in which a thin film is formed in a thickness ranging from several nano meters to several hundreds of nano meters in a liquid phase process. In the liquid phase process, a prescribed material used for the formation of a thin film is dissolved or dispersed to create a liquid matter, which is then subjected to the spin-coat method, dip method, or liquid-drop discharge method (or inkjet method) so as to produce the thin film. Herein, the spin-coat method and dip method are suited to the overall surface application, while the liquid-drop discharge method enables the thin film to be subjected to patterning at a prescribed location. For this reason, it is preferable in the hole transport layer forming process to use the liquid-drop discharge method, by which the hole transport layer forming material is applied onto the electrode surfaces 23c.

[0066]

In the case in which the selective application of the hole transport layer forming material is performed by the liquid-drop discharge method (or inkjet method), a liquid-drop discharge head (not shown) is firstly filled with the hole transport layer forming material; then, a discharge nozzle thereof is positioned to be opposite to the electrode surface 23c, which is located in the opening 25a of the lyophilic control layer 25. While the liquid-drop discharge head and the base material (i.e., substrate 20) are being moved relative to each other, the discharge nozzle discharges liquid drops, each of which is controlled in value, towards the electrode surface 23c.

[0067]

Thereafter, a drying process and a heating process are performed so as to evaporate the dispersion medium and/or solvent contained in the hole transport layer forming material, so that a thin film whose thickness ranges from several nano meters to several hundreds of nano meters is formed as the hole transport layer 70 on the electrode surface 23c. Preferably, the drying process is performed in the nitrogen atmosphere at the room temperature under the prescribed pressure of about 133.3 Pa (1

Torr). After the drying process, the heating process is performed preferably in the vacuum state at 200 °C for ten minutes or so.

[0068]

Liquid drops discharged from the discharge nozzle are spread on the electrode surface 23c, on which the lyophilic process was performed, so that they fill the opening 25a of the lyophilic control layer 25. On the other hand, liquid drops are repelled and not adhered on the upper surface of the organic bank layer 221, on which the lyophobic process was performed. Therefore, even when liquid drops deviate a prescribed discharged position and are unexpectedly discharged onto the upper surface of the organic bank layer 221, the upper surface of the organic bank layer 221 is not made wet so that repelled liquid drops may fall inside of the opening 25a of the lyophilic control layer 25.

After completion of the hole transport layer forming process, in order to avoid oxidation of the hole transport layer 70 and the luminescent layer 60, the subsequent processes are preferably performed in inert gas atmosphere such as a nitrogen atmosphere and an argon atmosphere.

[0069]

Next, as shown in FIG. 10(n), a luminescent layer forming process is performed to form the luminescent layer 60. In the luminescent layer forming process, the aforementioned liquid-drop discharge method is performed to discharge a luminescent layer forming material onto the hole transport layer 70; then, a drying process and a heating process are performed to form the luminescent layer 60 in the opening 221a of the organic bank layer 221. In the luminescent layer forming process, in order to avoid re-dissolution of the hole transport layer 70, the aforementioned nonpolar solvent insoluble to the hole transport layer 70 is used as solvent for use in the luminescent layer forming material.

[0070]

Specifically, in the luminescent layer forming process, the aforementioned liquid-drop discharge method is used to selectively apply a blue-color luminescent layer forming material to blue-color display regions, which are then subjected to a drying process. Similarly, the liquid-drop discharge method is performed so as to respectively apply green-color and red-color luminescent layer forming materials to green-color and

red-color display regions, which are then subjected to drying processes. In the case in which the liquid-drop discharge method is used to apply the aforementioned material to the designated color display regions, the drying process is performed in such a way that the substrate is heated on a hot plate (not shown) at a prescribed temperature, which is 200 °C or less, so that liquid content is dried and evaporated. In the case in which the spin-coat method or dip method is performed to apply the aforementioned material to the designated color display regions, nitrogen is sprayed onto the substrate, or the substrate is rotated to cause air flow on the surface thereof and is thus dried.

[0071]

Next, as shown in FIG. 10(o), an electron transport layer forming process is performed to form the electron transport layer 65. In the electron transport layer forming process, the aforementioned liquid-drop discharge method is performed to discharge the electron transport layer forming material, an LiF dispersion solution or a NaF aqueous solution, is discharged selectively onto the blue-color luminescent layers 60 and are then subjected to drying and heating processes, so that the electron transport layers 65 are formed inside of the openings 221a of the organic bank layers 221. In this electron transport layer forming process, in order to avoid re-dissolution of the luminescent layers 60, a nonpolar solvent insoluble to the luminescent layers 60 is used as the solvent for use in the electron transport layer forming material.

In this electron transport layer forming process, the electron transport layer forming material is subjected to application and is then subjected to the drying process, in which the substrate is heated on a hot plate (not shown) at a prescribed temperature, which is 200 °C or less, and is thus dried so that water content is evaporated.

[0072]

Next, as shown in FIG. 10(p), a cathode layer forming process is performed to form the cathode 50, wherein a prescribed cathode material such as aluminum (Al) is transformed into a film by evaporation or sputtering, for example.

Thereafter, an enclosing process is performed to form the encapsulating substrate 30, wherein a dryer (or a drying agent) 45 is attached to the interior wall of the encapsulating substrate 30 in order to prevent water or oxygen from penetrating into the organic electroluminescence device; then, the space formed between the substrate 20 and the encapsulating substrate 30 is enclosed by the enclosing resin 40. A

thermosetting resin or an ultraviolet-setting resin is used for the enclosing resin 40. Incidentally, the enclosing process is preferably performed in the inert gas atmosphere such as nitrogen, argon, and helium.

As a result, the organic electroluminescence device 1 is manufactured by the aforementioned steps and processes. Herein, it is certainly confirmed that when applying voltage of 10 V or less between both electrodes, in particular, blue-color light is preferably emitted from the pixel electrode 23.

[0073]

In the manufacture of the organic electroluminescence device 1, the electron transport layer 65 is formed using the LiF dispersion solution or NaF aqueous solution as the electron transport layer forming material therefor. This allows the electron transport layer 65 to be reliably formed in the liquid phase process. Therefore, it is possible to eliminate the foregoing drawbacks, which are caused in the case of the formation in the gaseous phase process, such as unwanted cost increase, and unwanted exposure of the organic bed material and substrate in high-temperature environments.

In short, the manufacturing method of this invention is advantageous in efficiency and cost in manufacture and is readily adopted in mass production, wherein it is in particular effective in manufacture of large-screen displays whose substrate sizes are not necessarily limited because of the adoption of the liquid-drop discharge method. In addition, this manufacturing method does not need evaporation masks, which contributes to manufacture of high-resolution and fine displays. Furthermore, this manufacturing method will effectively accelerate developments for flexible displays using plastic substrates having low heat resistances.

Since the electron transport layer forming materials are applied to the liquid-drop discharge method, they can be selectively located and applied to prescribed positions. Specifically, the electron transport layer 65 is selectively formed on the blue-color luminescent layer 60. Thus, it is possible to form blue-color luminescence component having high luminance at a high efficiency.

[0074]

In general, among red, green, and blue colors, charge injection barriers between the cathode 50 and the luminescent layer 60 for blue color is higher than the one for red or green color, and the luminescence intensity of blue color is lower than the one of the

other colors. In the organic electroluminescence device 1 manufactured by the aforementioned method, the electron transport layer 65 is formed on the luminescent layer 60 emitting blue color. This increases an electron transport efficiency with respect to the luminescent layer 60 emitting blue color. In summary, the organic electroluminescence device 1 is superior in luminescence characteristics due to high luminance and high efficiency in light emission of luminescence components.

[0075]

The present embodiment is described as the back emission type. Of course, this invention is not necessarily limited to the back emission type and can be easily applied to the top emission type. In addition, this invention can be applied to the other type of display in which light is emitted from both sides.

[0076]

Next, an electronic device incorporating the aforementioned organic electroluminescence device will be described with reference to FIG. 11, which shows the exterior appearance of a portable telephone (or a cellular phone).

In FIG. 11, reference numeral 1000 designates the main body (or housing) of the portable telephone, and reference numeral 1001 designates a display incorporating the aforementioned organic electroluminescence device.

Since the electronic device of FIG. 11 comprises the display 1001 incorporating the organic electroluminescence device, the display 1001 demonstrates high display characteristics and may satisfy user's preference in visibility.

[Brief Description of the Drawings]

[Figure 1]

FIG. 1 is a circuit diagram showing the wiring structure of an organic electroluminescence device of the invention.

[Figure 2]

FIG. 2 is a plan view diagrammatically showing the layout and structure of the organic electroluminescence device of the invention.

[Figure 3]

FIG. 3 is a cross sectional view taken along line A-B in FIG. 2.

[Figure 4]

FIG. 4 is a cross sectional view taken along line C-D in FIG. 2.

[Figure 5]

FIG. 5 is an enlarged view showing essential parts of the cross-sectional structure shown in FIG. 3.

[Figure 6]

FIG. 6 is a cross sectional view showing steps in order of a manufacturing method of the organic electroluminescence device.

[Figure 7]

FIG. 7 is a cross sectional view showing steps next to the steps shown in FIG. 6.

[Figure 8]

FIG. 8 is a cross sectional view showing steps next to the steps shown in FIG. 7.

[Figure 9]

FIG. 9 is a cross sectional view showing steps next to the steps shown in FIG. 8.

[Figure 10]

FIG. 10 is a cross sectional view showing steps next to the steps shown in FIG. 9.

[Figure 11]

FIG. 11 is a perspective view showing an exterior appearance of an electronic device of the invention.

[Brief Description of the Reference Symbols]

1 : ORGANIC ELECTROLUMINESCENCE DEVICE

23 : PIXEL ELECTRODE (ANODE)

50 : CATHODE

60 : LUMINESCENT LAYER

65 : ELECTRON TRANSPORT LAYER

[Document Type] Abstract

[Abstract]

[Problem to be Solved] To provide a manufacturing method for an organic electroluminescence device in which prescribed layers are formed in the liquid phase process using alkali metals and alkali earth metals, which produce good results in the conventional gaseous process, as well as halides (e.g., LiF) and oxides of rare earth metals, and to provide an electronic device using the aforementioned organic electroluminescence device.

[Means to Solve the Problem] An organic electroluminescence device basically comprises luminescent layers 60 arranged between an anode 23 and a cathode 50, which are arranged opposite to each other. An manufacturing method of this invention includes forming electron transport layers 65B, 65RG with introducing electron transport layer forming materials in a liquid phase process between the luminescent layers 60 and the cathode 50, the electron transport layer forming material including a prescribed element that is selected from among a halide or an oxide of an alkali metal, an alkali earth metal, and a rare earth metal.

[Elected Drawing] FIG. 5